



3DD262(3DD263)

NPN Silicon Low Frequency High Power Transistor



Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications					Test Condition
			A	B	C	D	E	
Collector-Emitter Voltage	V _{CEO}	V	300	400	500	600	700	
Emitter-Base Voltage	V _{EBO}	V	5					
Max. Collector Current	I _{CM}	A	5					
Max. Collector Dissipation	P _{CM}	W	75					Tc:75°C
Junction Temperature	T _{jm}	°C	175					
Storage Temperature	T _{stg}	°C	-55~+175					
Collector-Emitter Leakage Current	I _{CEO}	mA	Max.:1.0					V _{CE} =100V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	Max.:1.5					I _C =2.5A,I _B =0.5A
DC Current Gain	h _{FE}		Min.:7,Max.:180					V _{CE} =10V,I _C =2.5A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	A	B	C	D	E	I _C =3mA
			300	400	500	600	700	
E-Base Breakdown Voltage	V _{(BR)EBO}	V	5					I _E =2mA

hFE Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue	Purple
h _{FE}	7~15	15~25	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions: